

Low Temp Curing & High Rs & Chemical Resistance Color Resist SECR-RGBY702(10% ZrO₂ in Solid)

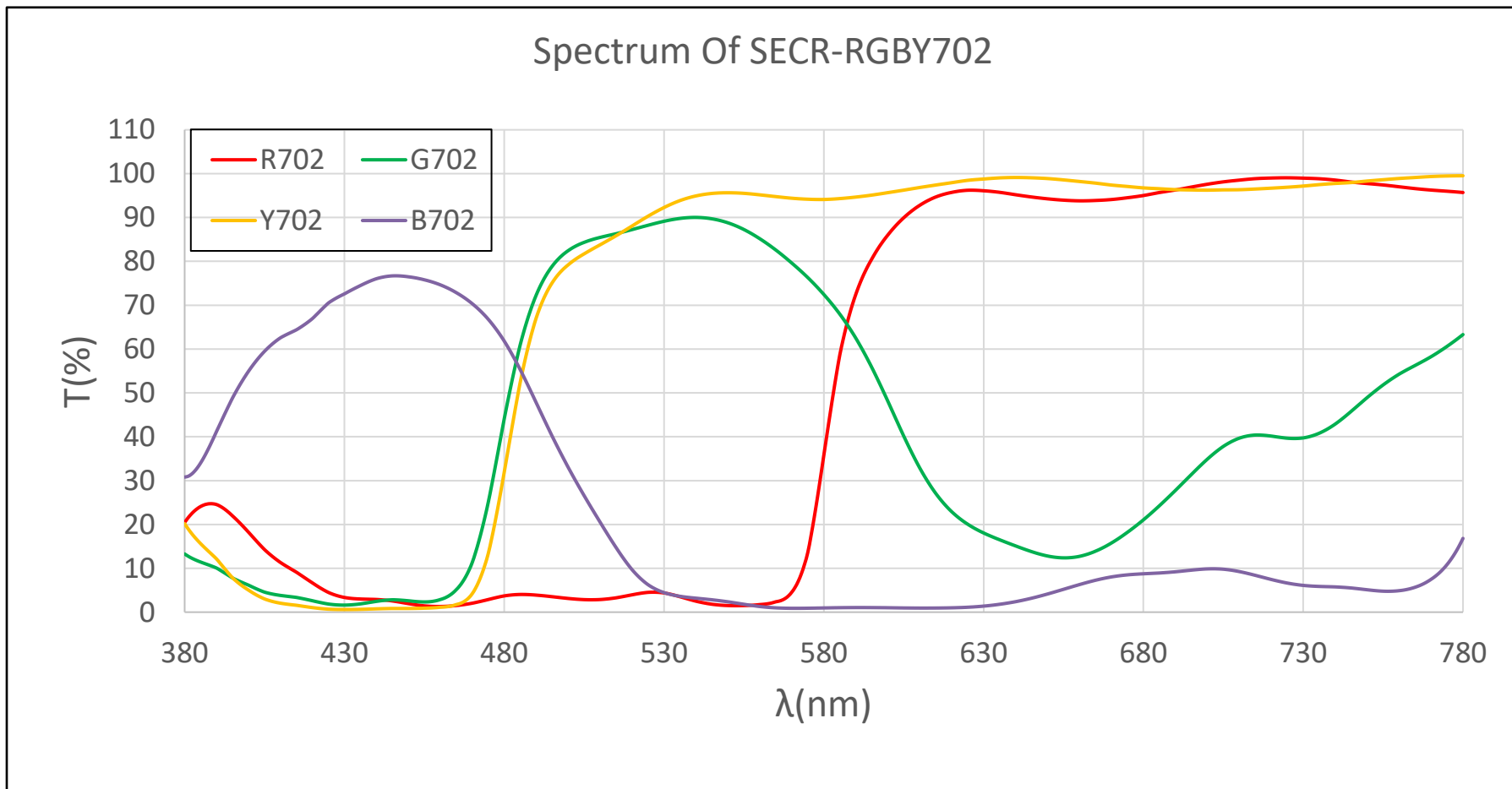
Product	Vis. (cps)	ZrO ₂ (%)	BT/ Dev. Time (sec)	Trans. % (At 450nm)	Y	x	y	THK(μm) (under 400rpm)	Adhesion (μm)
R702	4.5	10	9/ 18	2.13	24.83	0.6152	0.3449	1.14	5
G702	4.1	10	5/ 10	5.28	68.13	0.3379	0.5152	1.05	5
B702	4.1	10	17/ 32	4.16 (530nm)	8.32	0.1482	0.0789	1.19	5
Y702	4.0	10	6/ 12	0.82	83.57	0.4301	0.4988	1.01	5

Process Parameter	
Spin Speed	400rpm on 0.5mm EXG
THK	Control at 1.1~1.25μm before Post-bake
Pre-bake	90°C*2.5min, directly
Power	80mJ/ cm ² & Gap=0μm @25mW/ cm ²
Dev.	10~20 sec in 1:99 SEDR-5/ 0.15MPa & 25 °C
Rinse	20sec/ 0.15MPa & 25 °C
HPMJ	10sec/ 0.4MPa & 25 °C
Post-bake	200 °C*30min clean oven

Product	Condition
	After 200°C*30min_Dipping in PGMEA*600sec
R702	5μm/ 5B
G702	5μm/ 5B
B702	5μm/ 5B
Y702	5μm/ 5B

Surface Status			
Percent Area Removed	0% None	Less than 5%	5~15%
Classification	5B	4B	3B
Surface Status			
Percent Area Removed	13~35%	35~65%	Great than 65%
Classification	2B	1B	0B

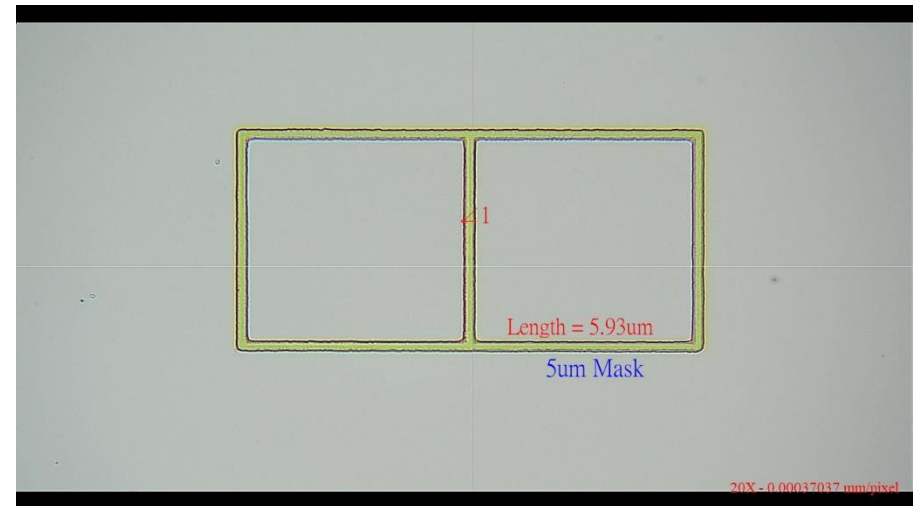
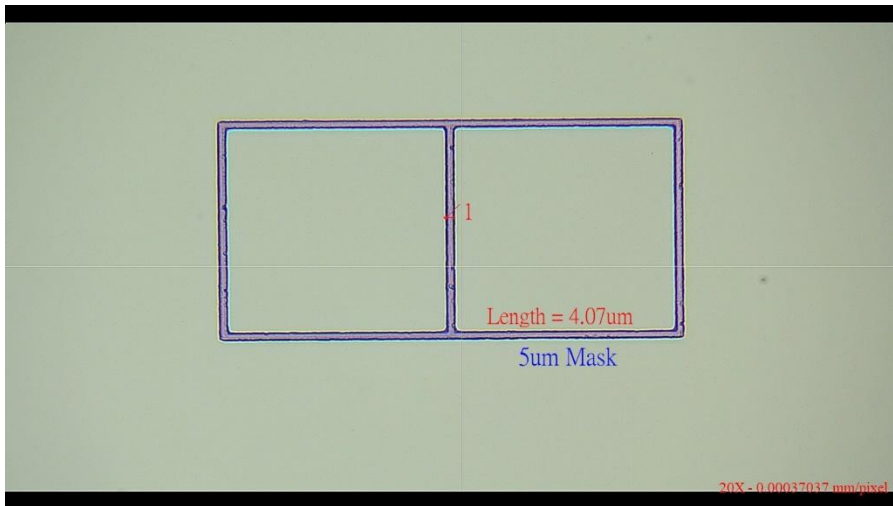
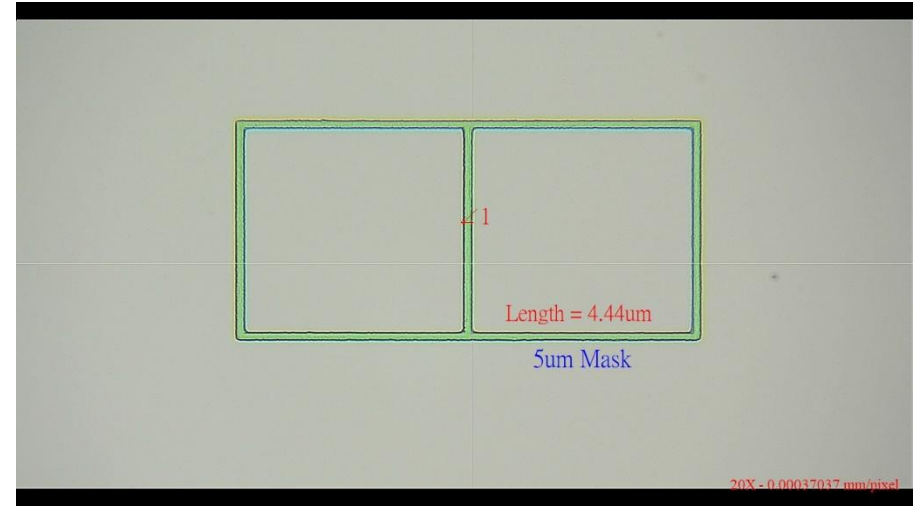
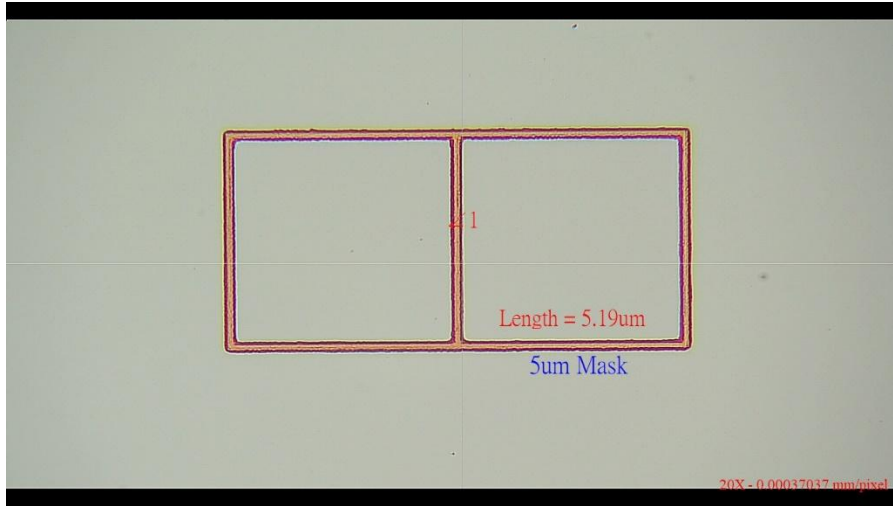
SPECTRUM



THK=1.0~1.15μm, Exp. Dose=80mJ/cm², Gap=0μm, Dev.=10~20s, Postbake=200°C *30min

All Right Reserved. Please don't copy or forward without authorizations of SynthEdge Advanced Materials Co., Ltd.

Profile ~ 5 μ m Pattern OM



THK=1.0~1.15 μ m, Exp. Dose=80mJ/cm², Gap=0 μ m, Dev.=10~20s, Postbake=200 $^{\circ}$ C *30min

All Right Reserved. Please don't copy or forward without authorizations of SynthEdge Advanced Materials Co., Ltd.